

# **SPZT751T1G Datasheet**



https://www.DiGi-Electronics.com

DiGi Electronics Part Number SPZT751T1G-DG

Manufacturer onsemi

Manufacturer Product Number SPZT751T1G

Description TRANS PNP 60V 2A SOT223

Detailed Description Bipolar (BJT) Transistor PNP 60 V 2 A 75MHz 800 mW

Surface Mount SOT-223 (TO-261)



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

DiGi is a global authorized distributor of electronic components.



# **Purchase and inquiry**

Manufacturer Product Number:	Manufacturer:
SPZT751T1G	onsemi
Series:	Product Status:
	Active
Transistor Type:	Current - Collector (Ic) (Max):
PNP	2 A
Voltage - Collector Emitter Breakdown (Max):	Vce Saturation (Max) @ lb, lc:
60 V	500mV @ 200mA, 2A
Current - Collector Cutoff (Max):	DC Current Gain (hFE) (Min) @ Ic, Vce:
100nA (ICBO)	75 @ 1A, 2V
Power - Max:	Frequency - Transition:
800 mW	75MHz
Operating Temperature:	Mounting Type:
150°C (TJ)	Surface Mount
Package / Case:	Supplier Device Package:
TO-261-4, TO-261AA	SOT-223 (TO-261)
Base Product Number:	
CD7T751	

# **Environmental & Export classification**

8541.21.0095

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	



# PNP Silicon Planar Epitaxial Transistor PZT751T1

This PNP Silicon Epitaxial transistor is designed for use in industrial and consumer applications. The device is housed in the SOT-223 package which is designed for medium power surface mount applications.

### **Features**

- High Current
- The SOT-223 Package can be soldered using wave or reflow.
- SOT-223 Package Ensures Level Mounting, Resulting in Improved Thermal Conduction, and Allows Visual Inspection of Soldered Joints. The Formed Leads Absorb Thermal Stress During Soldering, Eliminating the Possibility of Damage to the Die
- NPN Complement is PZT651T1G
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant\*

### MAXIMUM RATINGS (T<sub>C</sub> = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V <sub>CEO</sub>	-60	Vdc
Collector-Base Voltage	V <sub>CBO</sub>	-80	Vdc
Emitter-Base Voltage	V <sub>EBO</sub>	-5.0	Vdc
Collector Current	Ic	-2.0	Adc
Total Power Dissipation @ T <sub>A</sub> = 25°C (Note 1) Derate above 25°C	P <sub>D</sub>	0.8 6.4	W mW/°C
Storage Temperature Range	T <sub>stg</sub>	-65 to 150	°C
Junction Temperature	TJ	150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

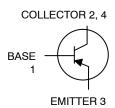
### THERMAL CHARACTERISTICS

Rating	Symbol	Value	Unit
Thermal Resistance from Junction-to- Ambient in Free Air	$R_{\theta JA}$	156	°C/W
Maximum Temperature for Soldering Purposes	TL	260	°C
Time in Solder Bath		10	Sec

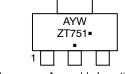
<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

# SOT-223 PACKAGE HIGH CURRENT NPN SILICON TRANSISTOR SURFACE MOUNT





#### MARKING DIAGRAM



A = Assembly Location

Y = Year W = Work Week

■ = Pb-Free Package

(Note: Microdot may be in either location)

### ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
PZT751T1G	SOT-223 (Pb-Free)	1,000 / Tape & Reel
SPZT751T1G	SOT-223 (Pb-Free)	1,000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

1

Device mounted on a FR-4 glass epoxy printed circuit board using minimum recommended footprint.

# PZT751T1

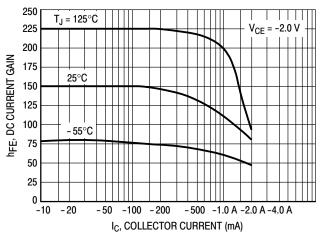
# **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristics	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Breakdown Voltage ( $I_C = -10$ mAdc, $I_B = 0$ )	V <sub>(BR)</sub> CEO	-60	_	Vdc
Collector–Emitter Breakdown Voltage ( $I_C = -100 \mu Adc$ , $I_E = 0$ )	V <sub>(BR)</sub> CBO	-80	_	Vdc
Emitter–Base Breakdown Voltage ( $I_E = -10 \mu Adc, I_C = 0$ )	V <sub>(BR)EBO</sub>	-5.0	_	Vdc
Base-Emitter Cutoff Current (V <sub>EB</sub> = -4.0 Vdc)	I <sub>EBO</sub>	_	-0.1	μAdc
Collector-Base Cutoff Current (V <sub>CB</sub> = -80 Vdc, I <sub>E</sub> = 0)	I <sub>CBO</sub>	_	-100	nAdc
ON CHARACTERISTICS (Note 2)	•			
DC Current Gain ( $I_C = -50 \text{ mAdc}$ , $V_{CE} = -2.0 \text{ Vdc}$ ) ( $I_C = -500 \text{ mAdc}$ , $V_{CE} = -2.0 \text{ Vdc}$ ) ( $I_C = -1.0 \text{ Adc}$ , $V_{CE} = -2.0 \text{ Vdc}$ ) ( $I_C = -2.0 \text{ Adc}$ , $V_{CE} = -2.0 \text{ Vdc}$ )	h <sub>FE</sub>	75 75 75 40	- - - -	-
Collector–Emitter Saturation Voltages ( $I_C$ = -2.0 Adc, $I_B$ = -200 mAdc) ( $I_C$ = -1.0 Adc, $I_B$ = -100 mAdc)	V <sub>CE(sat)</sub>	- -	-0.5 -0.3	Vdc
Base-Emitter Voltages (I <sub>C</sub> = -1.0 Adc, V <sub>CE</sub> = -2.0 Vdc)	V <sub>BE(on)</sub>	_	-1.0	Vdc
Base–Emitter Saturation Voltage ( $I_C = -1.0$ Adc, $I_B = -100$ mAdc)	V <sub>BE(sat)</sub>	_	-1.2	Vdc
Current–Gain–Bandwidth (I <sub>C</sub> = -50 mAdc, V <sub>CE</sub> = -5.0 Vdc, f = 100 MHz)	f <sub>T</sub>	75	-	MHz

<sup>2.</sup> Pulse Test: Pulse Width  $\leq$  300  $\mu\text{s},$  Duty Cycle = 2.0%.

## PZT751T1

## **TYPICAL CHARACTERISTICS**



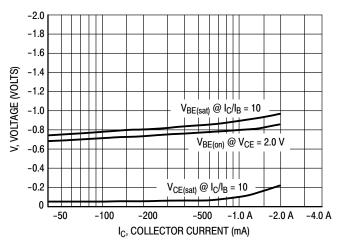
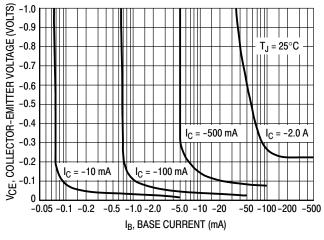


Figure 1. Typical DC Current Gain

Figure 2. On Voltages



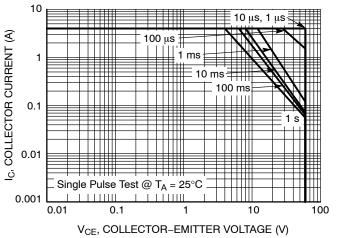


Figure 3. Collector Saturation Region

Figure 4. Safe Operating Area

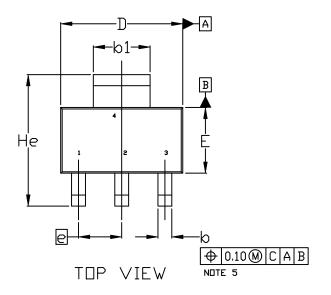


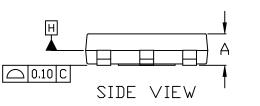
# **MECHANICAL CASE OUTLINE**

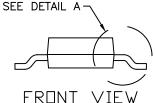
PACKAGE DIMENSIONS

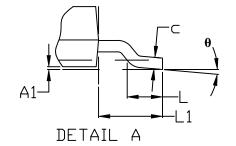


**DATE 02 OCT 2018** 





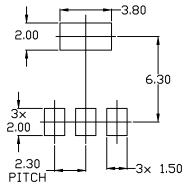




#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- CONTROLLING DIMENSION: MILLIMETERS
- DIMENSIONS D & E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH, PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.200MM PER SIDE.
- 4. DATUMS A AND B ARE DETERMINED AT DATUM H.
- A1 IS DEFINED AS THE VERTICAL DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT OF THE PACKAGE BODY.
- POSITIONAL TOLERANCE APPLIES TO DIMENSIONS b AND b1.

	MILLIMETERS				
DIM	MIN.	MIN. NOM. MA			
Α	1.50	1.63	1.75		
A1	0.02	0.06	0.10		
b	0.60	0.75	0.89		
b1	2.90	3.06	3.20		
c	0.24	0.29	0.35		
D	6.30	6.50	6.70		
E	3.30	3.50	3.70		
е		2.30 BSC	;		
L	0.20				
L1	1.50	1.75	2.00		
He	6.70	7.00	7.30		
θ	0*		10°		



RECOMMENDED MOUNTING **FOOTPRINT** 

DOCUMENT NUMBER:	98ASB42680B	Electronic versions are uncontrolled except when accessed directly from the Document Reposito Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	SOT-223 (TO-261)		PAGE 1 OF 2

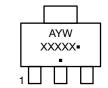
onsemi and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves brisefin and of 160 m are trademarked so defined values of services and of the confined values and of the values of the confined values and of the values of the confined values and of the values of the v special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

# **SOT-223 (TO-261)** CASE 318E-04 ISSUE R

**DATE 02 OCT 2018** 

STYLE 1: PIN 1. BASE 2. COLLECTOR 3. EMITTER 4. COLLECTOR	STYLE 2: PIN 1. ANODE 2. CATHODE 3. NC 4. CATHODE	STYLE 3: PIN 1. GATE 2. DRAIN 3. SOURCE 4. DRAIN	STYLE 4: PIN 1. SOURCE 2. DRAIN 3. GATE 4. DRAIN	STYLE 5: PIN 1. DRAIN 2. GATE 3. SOURCE 4. GATE
STYLE 6: PIN 1. RETURN 2. INPUT 3. OUTPUT 4. INPUT	STYLE 7: PIN 1. ANODE 1 2. CATHODE 3. ANODE 2 4. CATHODE	STYLE 8: CANCELLED	STYLE 9: PIN 1. INPUT 2. GROUND 3. LOGIC 4. GROUND	STYLE 10: PIN 1. CATHODE 2. ANODE 3. GATE 4. ANODE
STYLE 11: PIN 1. MT 1 2. MT 2 3. GATE 4. MT 2	STYLE 12: PIN 1. INPUT 2. OUTPUT 3. NC 4. OUTPUT	STYLE 13: PIN 1. GATE 2. COLLECTOR 3. EMITTER 4. COLLECTOR		

# GENERIC MARKING DIAGRAM\*



A = Assembly Location

Y = Year

W = Work Week
XXXXX = Specific Device Code

= Pb-Free Package

(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

DOCUMENT NUMBER:	98ASB42680B	B42680B Electronic versions are uncontrolled except when accessed directly from the Document Reposi Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	SOT-223 (TO-261)		PAGE 2 OF 2

onsemi and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

onsemi, ONSEMI, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at <a href="www.onsemi.com/site/pdf/Patent-Marking.pdf">www.onsemi.com/site/pdf/Patent-Marking.pdf</a>. onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that onsemi was negligent regarding the design or manufacture of the part. onsemi is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

### ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

 $\textbf{Technical Library:} \ \underline{www.onsemi.com/design/resources/technical-documentation}$ 

onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at www.onsemi.com/support/sales



# **OUR CERTIFICATE**

DiGi provide top-quality products and perfect service for customer worldwide through standardization, technological innovation and continuous improvement. DiGi through third-party certification, we striciy control the quality of products and services. Welcome your RFQ to Email: Info@DiGi-Electronics.com

















Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com